

VFE upgrade



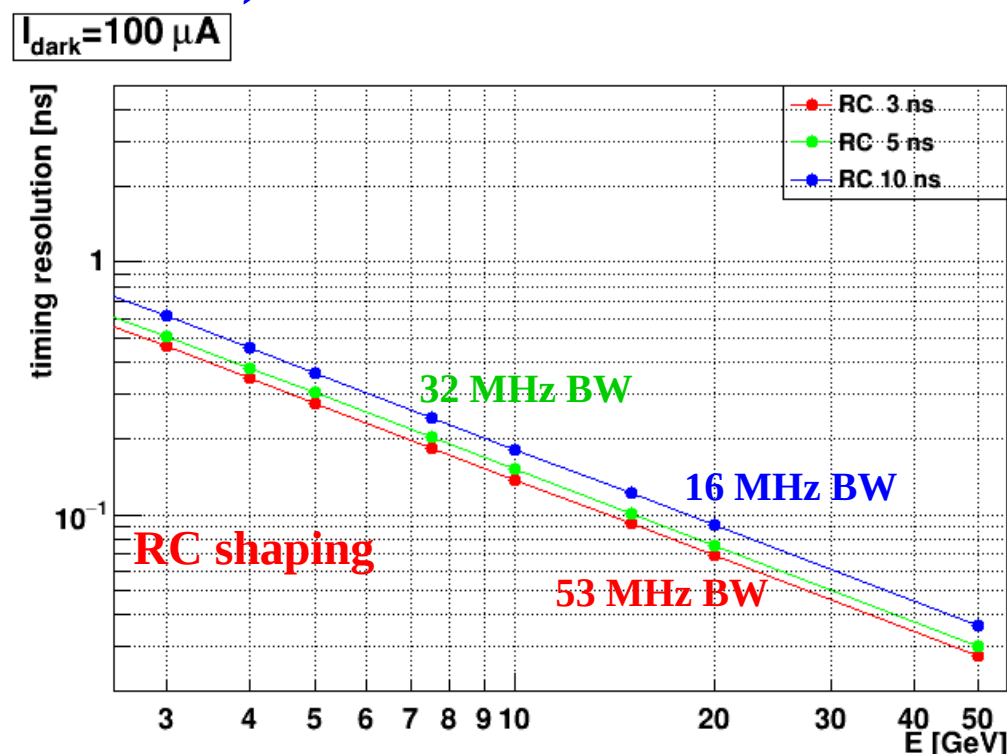
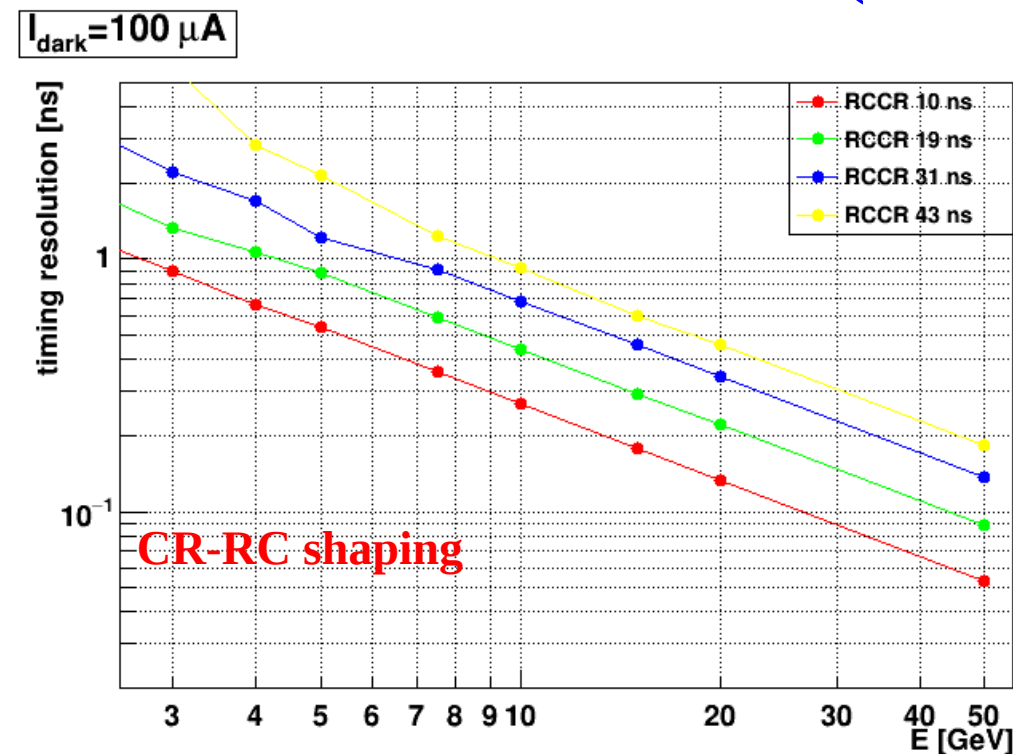
Progress report

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Short term planning

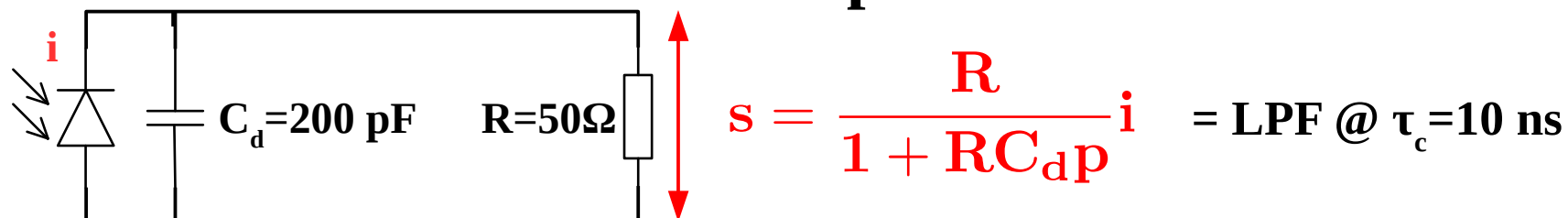
- **Get rock-solid inputs for TDR redaction and further studies/simulations**
 - **Pulse shapes**
 - ▶ **Scintillation**
 - ▶ **Spikes**
 - **Noise models**
 - ▶ **APD leakage current**
 - **ADC**
 - ▶ **Get VFE performances vs digitization step and sampling rate**
 - **Ultimate timing performances vs E and vs APD aging**
 - **Ultimate energy resolution vs APD aging**
- **How**
 - **Make measurements at TB with fast TIA to get realistic image of physical signals**
 - **Use multi-Gsample/sec ADC to simulate any scenario**

- Possibility to get good timing information with full signal information
 - Worst case scenario (see DN-2015/014)

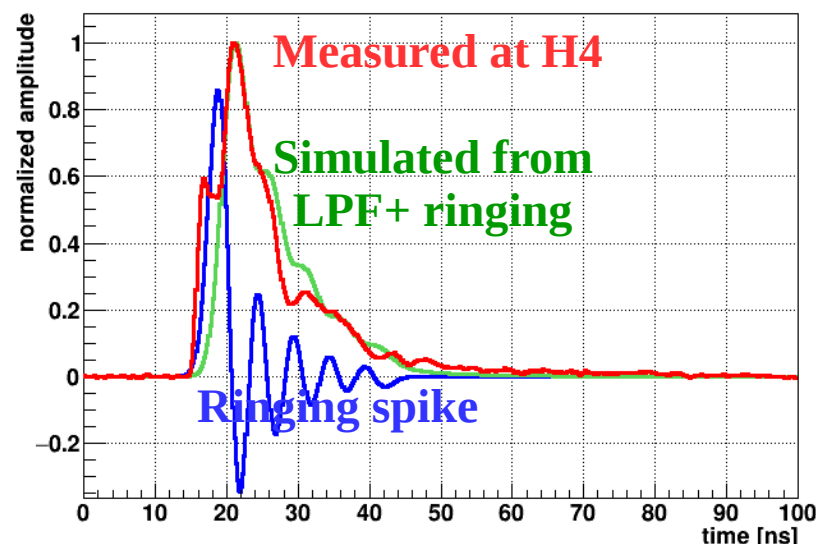
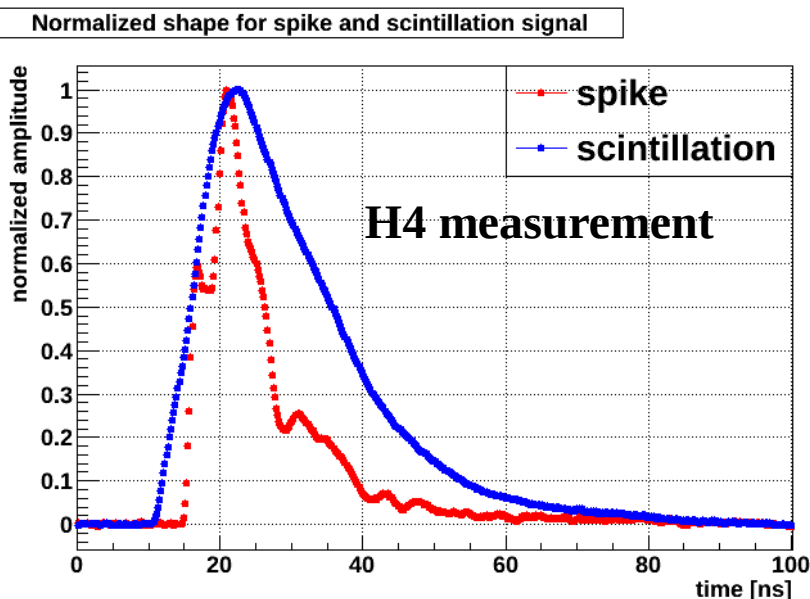


- Target : 50 MHz BW TIA
 - Validate performances at TB

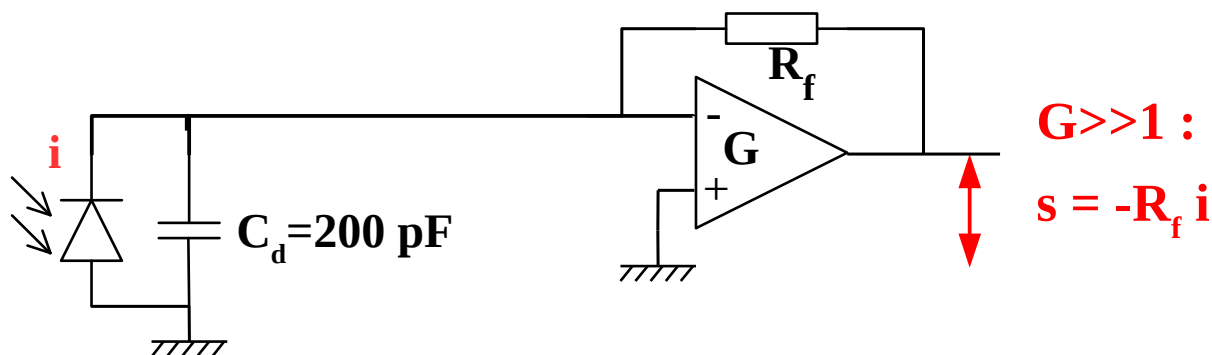
- Photo-detector has intrinsic capacitance :



- Direct connection of APD to digitizer
 - Low pass filter
 - Kapton connections = RLC circuit



- Isolate APD from digitizer
 - Keep high bandwidth signal
 - ▶ APD should see $0\ \Omega$ input impedance amplifier \rightarrow TIA
 - ▶ Very high open-loop gain (G) amplifier with feedback resistor (R_f):
 - Gain = $-R_f/(1+1/G)$
 - Input impedance : R_f/G



- **Requests**
 - **Ready and operational before TB (June ?)**
 - ▶ **Use of discrete components (No ASIC)**
 - ▶ **Work on ASIC study in parallel**
 - **50 MHz TIA**
 - ▶ **Should be able to test ultimate timing performances**
 - ▶ **Shape measurements**
 - **Low noise (as low as possible)**
 - ▶ **Should be able to validate APD noise model**
 - **100 MeV- 2TeV dynamics**
 - **2 outputs : Gain 1 and gain 10**
 - ▶ **Simulate gain switching at LHC**
 - **CMS-ECAL geometry**
 - ▶ **Should plug on Mother Boards**

- Use discrete components
 - Operational amplifiers
- 50 MHz Bandwidth
 - Constraint from APD capacitance
 - ▶ Need > 650 MHz Op-Amp Bandwidth (GBWP)
 - Need to “compensate” the gain loop for stability
 - ▶ Capacitor in parallel to gain resistor

● Noise sources:

● APD leakage current :

$$\tilde{i}_{\text{APD}} = \sqrt{2I_d q_e (\epsilon + \text{MF}(1 - \epsilon)) \Delta f} = 5.4 \sqrt{I_d} \text{ nA}/\sqrt{\text{Hz}}$$

● Op-amp input current noise :

$$\tilde{i}_{\text{OA}} \approx 2.5 \text{ pA}/\sqrt{\text{Hz}}$$

● Op-amp input voltage noise :

$$\tilde{e}_{\text{OA}} \approx 1.0 \text{ nV}/\sqrt{\text{Hz}}$$

● Total output noise :

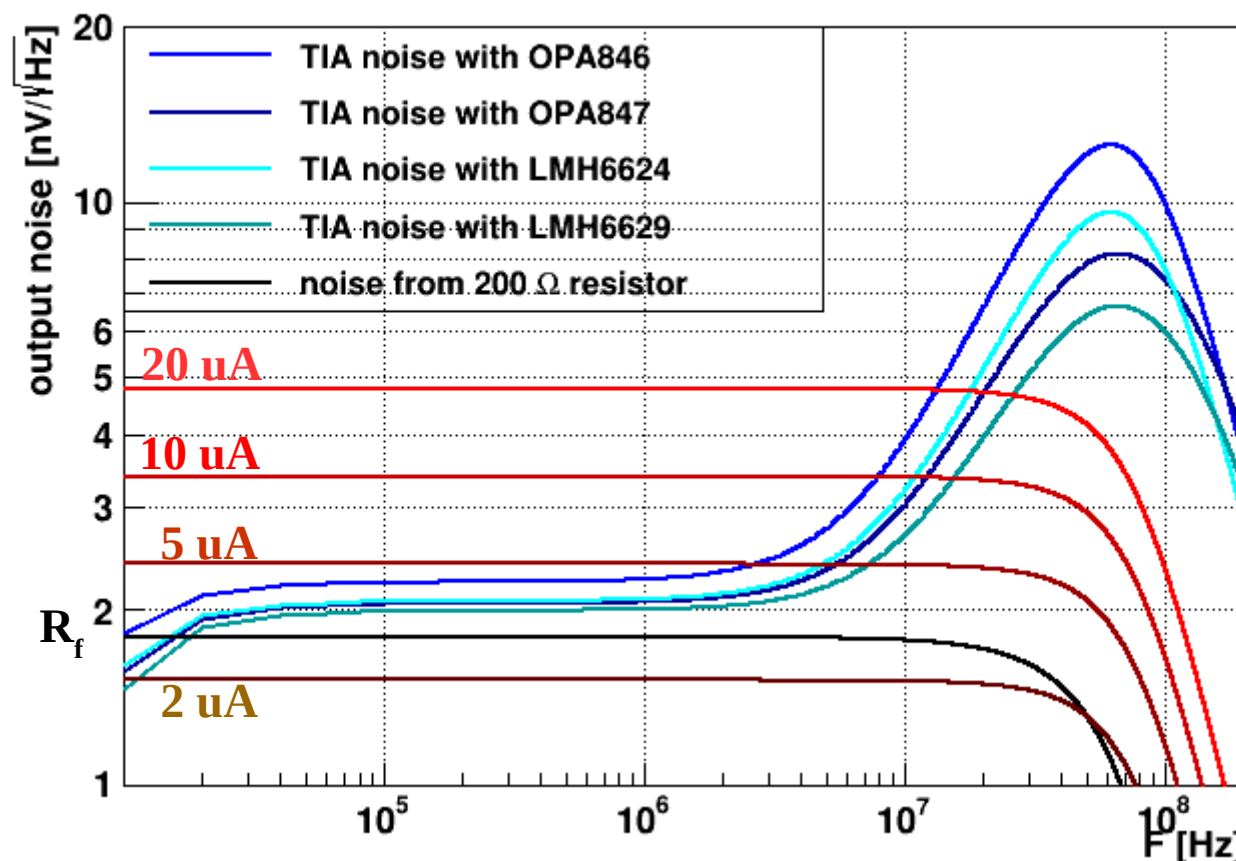
$$\tilde{s} = \sqrt{|H|^2 \tilde{i}_{\text{leak}}^2 + |H|^2 \tilde{i}_{\text{OA}}^2 + \left| \frac{1 + \frac{R_f}{Z_d}}{1 + \frac{1}{G} \left(1 + \frac{R_f}{Z_d} \right)} \right|^2 \tilde{e}_{\text{OA}}^2}$$

► $|R_f/Z_d| \sim R_f C_d 2\pi F$

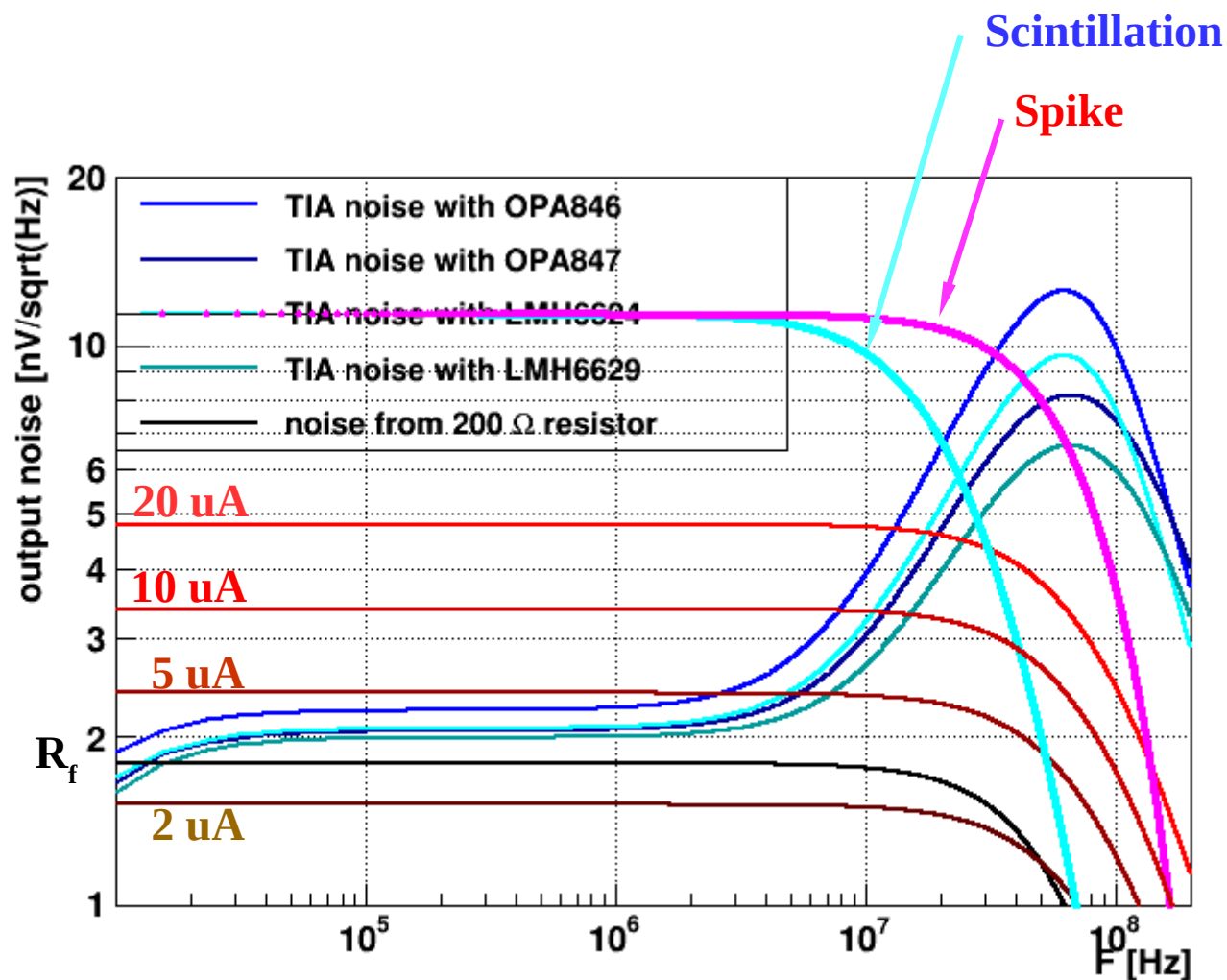
► Rise at high frequencies !

Theory : Expected TIA noise-2

- Compute noise with various amplifiers
- Compare with expected noise from APD leakage current



- Compare with signals





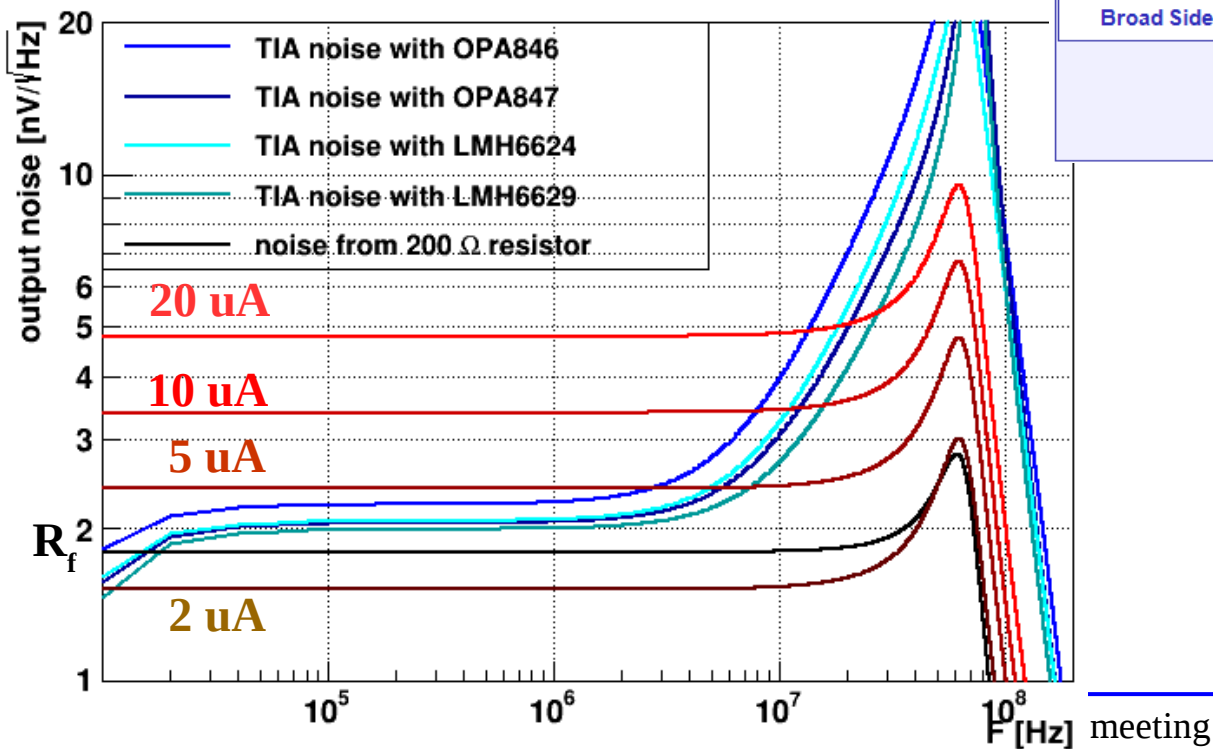
Fit with ECAL geometry : Effect of APD kaptons



● Add inductance between APD and TIA

● Estimated to 2.4pF/cm and 1.6 nH/cm

- ▶ Huge distortion of frequency response
- ▶ Noise enhancement

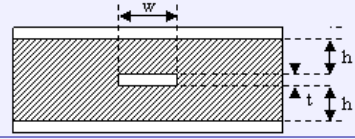


Calculator Group: PCB Stripline Structures Show All

Stripline Impedance Calculator

Note: valid for (w/h) from 0.1 to 2.0 and (t/h) less than 0.25
Dimensional units: ☒ mm ☐ mils

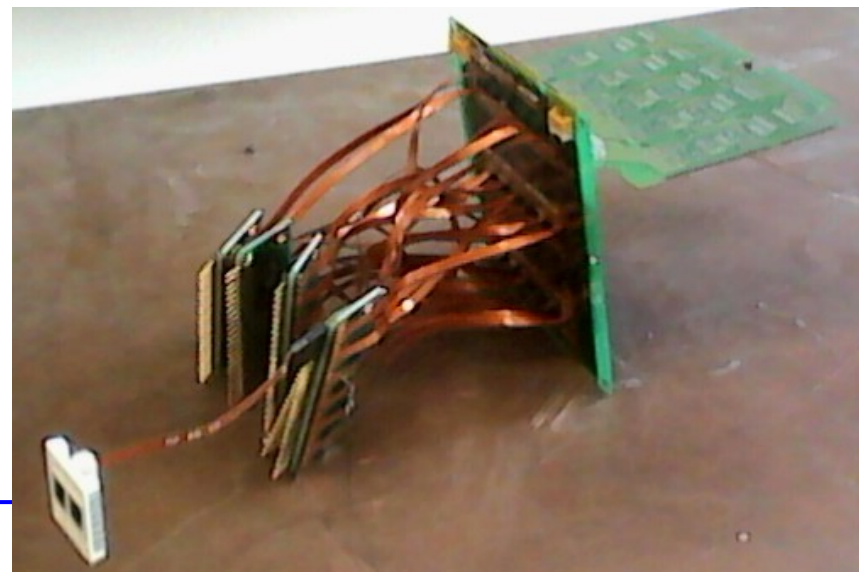
w (trace width) =	0.150
t (trace thickness) =	0.035
h (dielectric thickness) =	0.075
er (relative dielectric constant) =	3.5



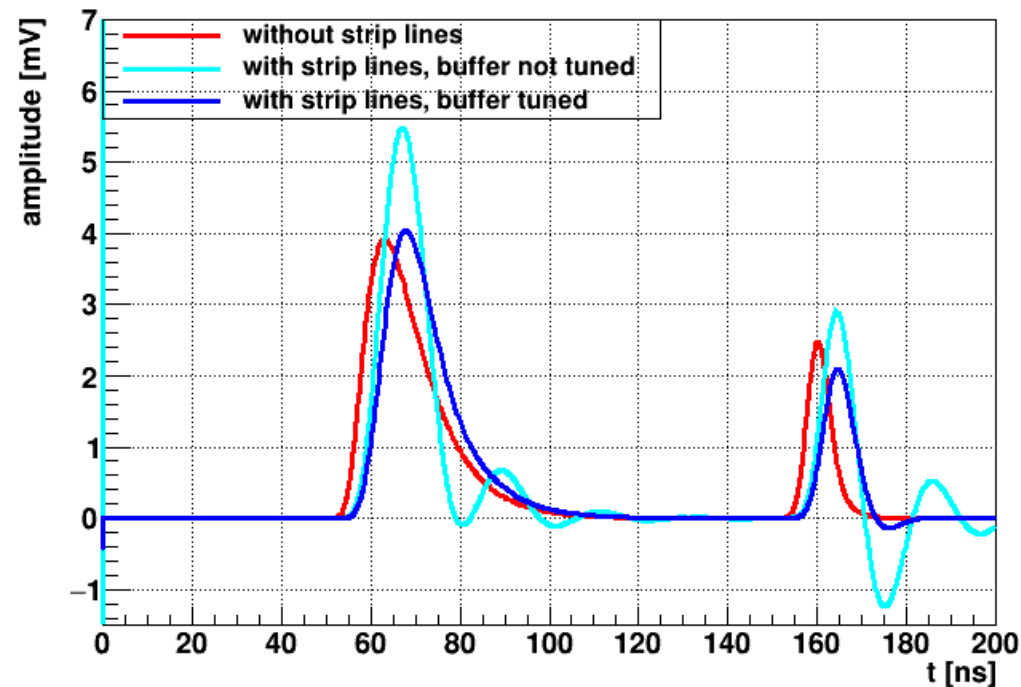
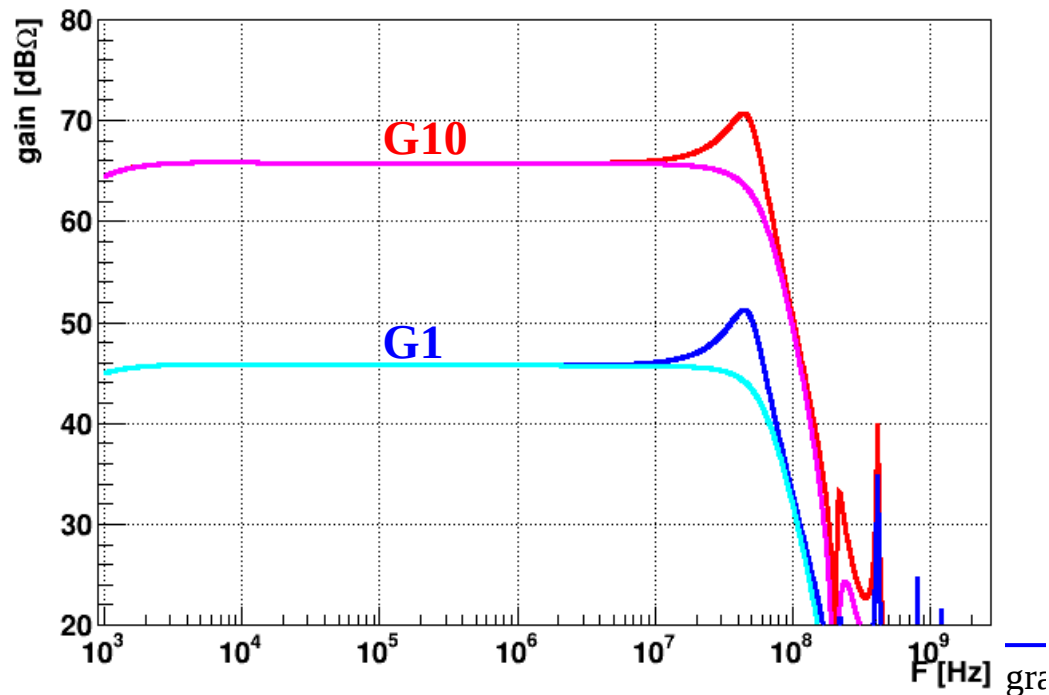
Calculate

Z ₀ (Impedance, Ohms) =	26.260
Propagation Delay, T _{pd} (ps/cm) =	62.355
Inductance, L (nH/cm) =	1.637
Capacitance, C (pF/cm) =	2.37456

Note: 1oz = 1.4mils = 0.03556mm

$$Z_0 = \frac{60}{\sqrt{\epsilon_r}} \ln \left(\frac{1.9(2h+t)}{(0.8w+t)} \right) \quad T_{pd} = 3.333 \sqrt{\epsilon_r} \left(\frac{ns}{meter} \right)$$


- Optimize design
 - Low Noise
 - Kapton effect:
 - ▶ $L_{\text{kapton}} C_{\text{APD}} \rightarrow 63 \text{ MHz resonator} \rightarrow \text{above } 50 \text{ MHz BW} \rightarrow \text{OK}$
 - Kapton mitigation : add serial (damping) resistor on APD line
 - ▶ Keep 50 MHz bandwidth
 - ▶ Restore pulse integrity



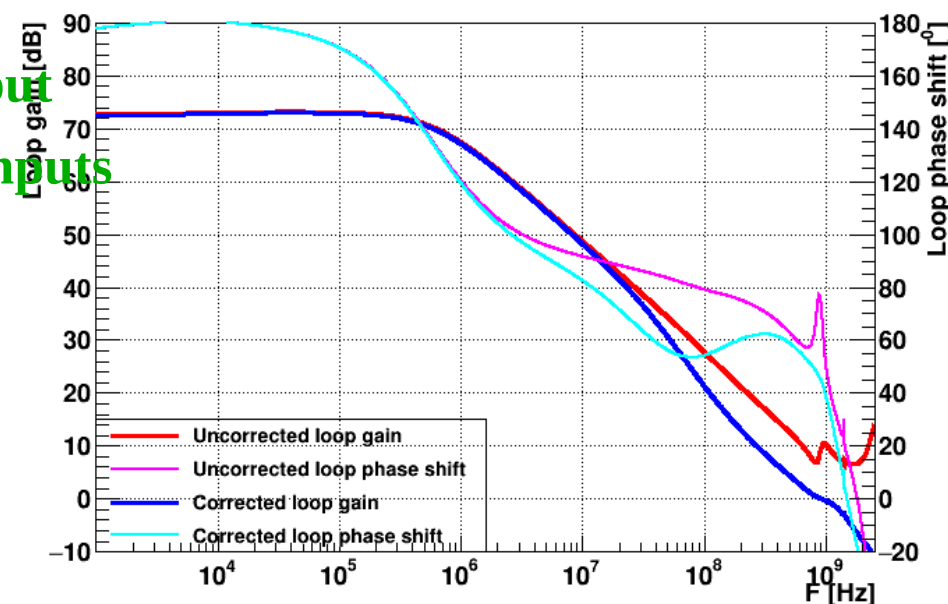
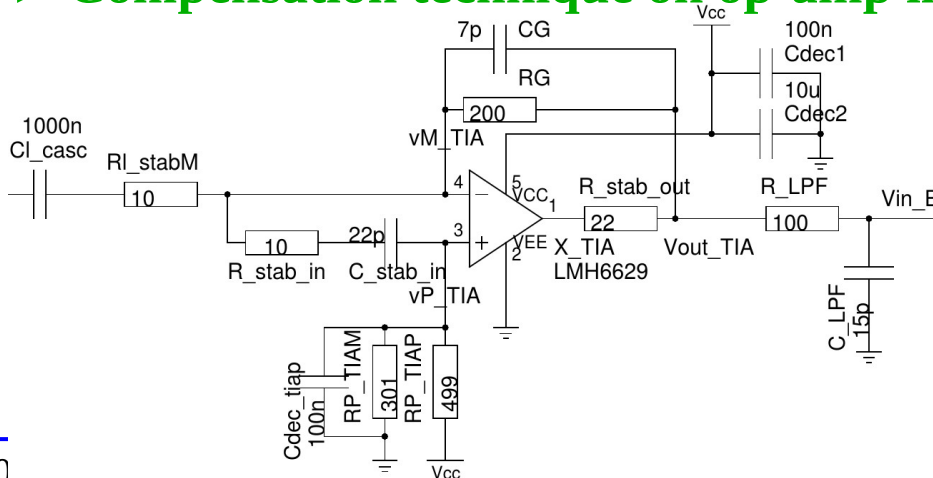
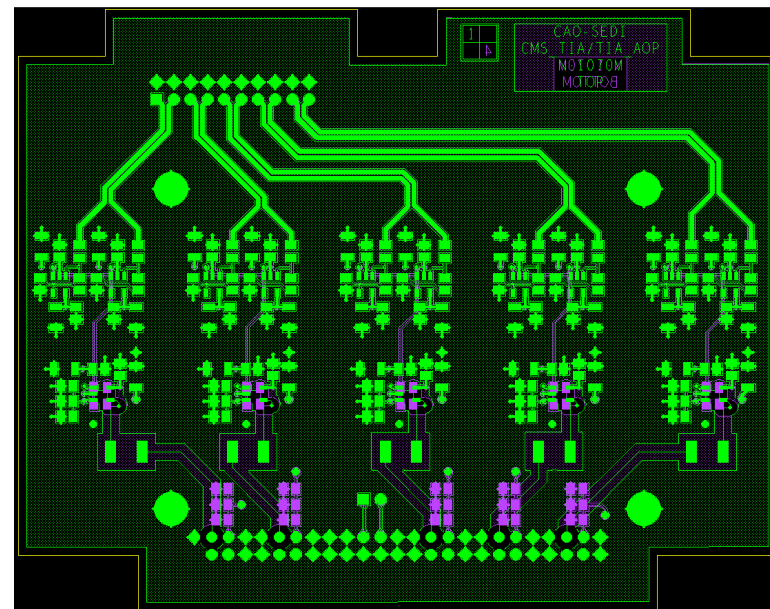
- Build a VFE board with Op-amp TIA

- 500 MHz Oscillator :(
- LMH6629 very sensitive to parasitic inductances
 - 0.55 nH/mm + 1.2 nH/via on PCB
 - Not taken into account

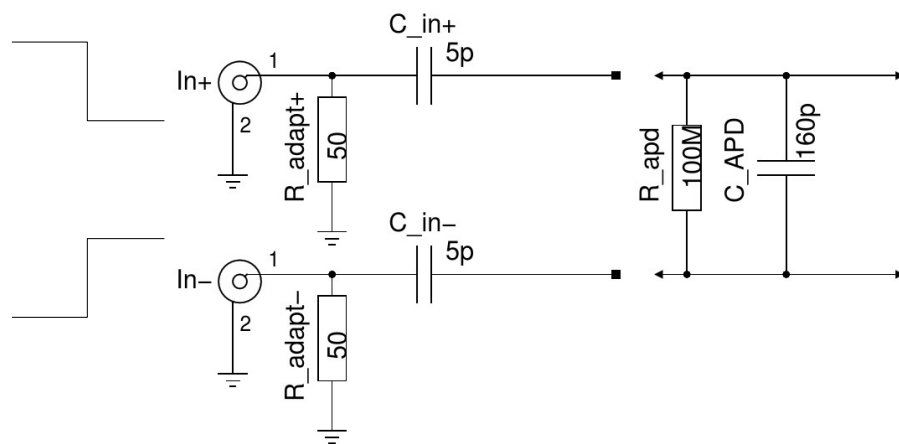
- Modify PCB in situ

- Restore phase margin

- Add damping resistor on op-amp output
- Compensation technique on op-amp inputs



- **Noise measurements**
 - Connect TIA output to Digital scope
 - ▶ Measure RMS
 - ▶ Measure noise density spectrum using FFT in Math tools
- **Signal Measurements**
 - Inject current pulses through capacitors [$i(t)=C \, dV/dt$]
 - ▶ Spike simulation using very fast edged signals (0.9 ns)

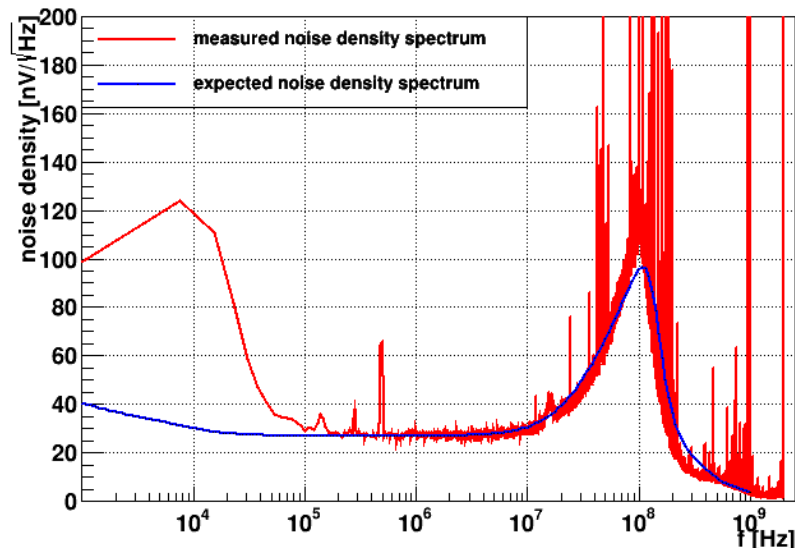


Spike injector

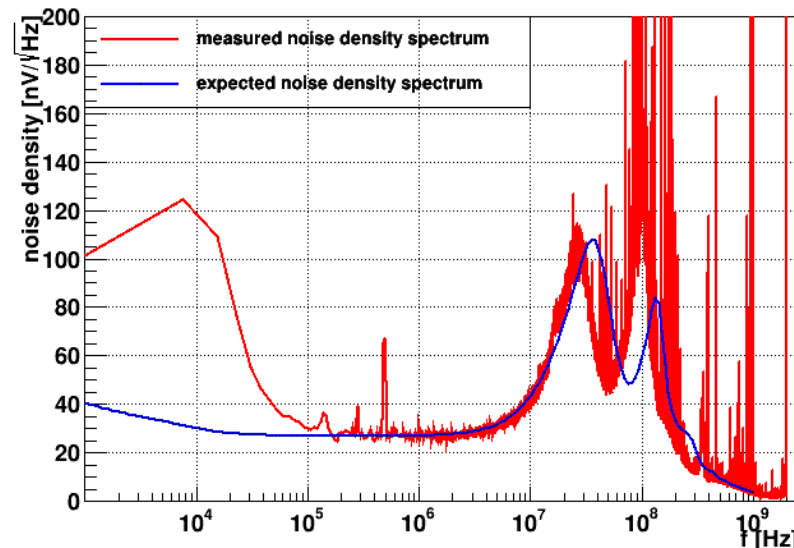
Noise generator

● Noise density spectra: Spice vs Measurements

F2fft-g10_noise-0pF_dB **No APD connected**

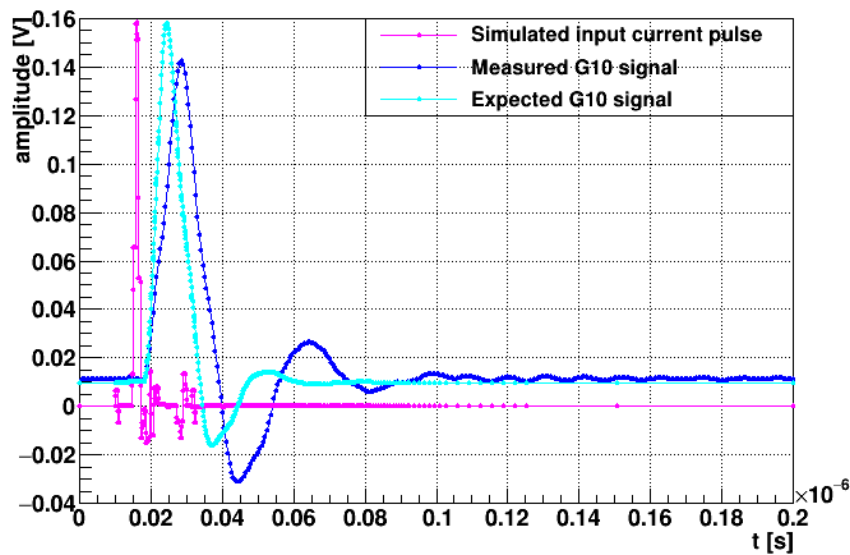


F2fft-g10_noise-164pF_dB **Fake APD connected**

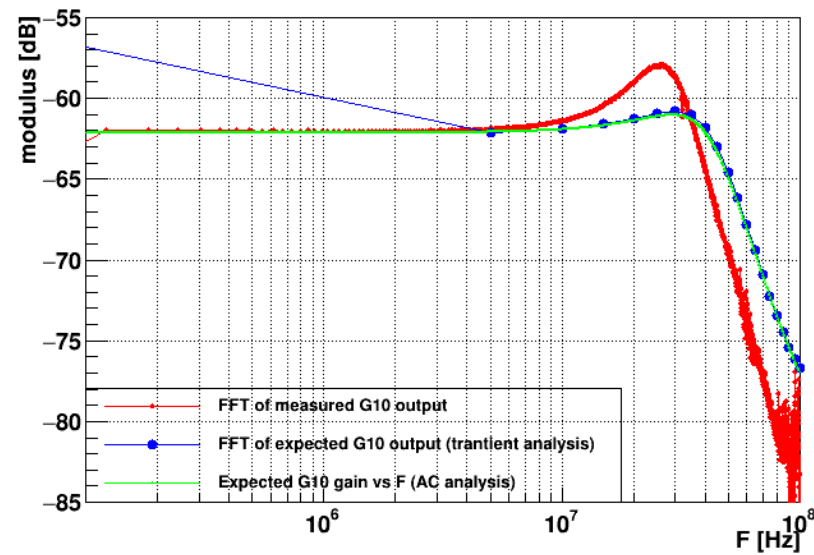


● Signal and spectrum: Spice vs Measurements

Simulation with 1.6nH/cm and 2.4pF/cm

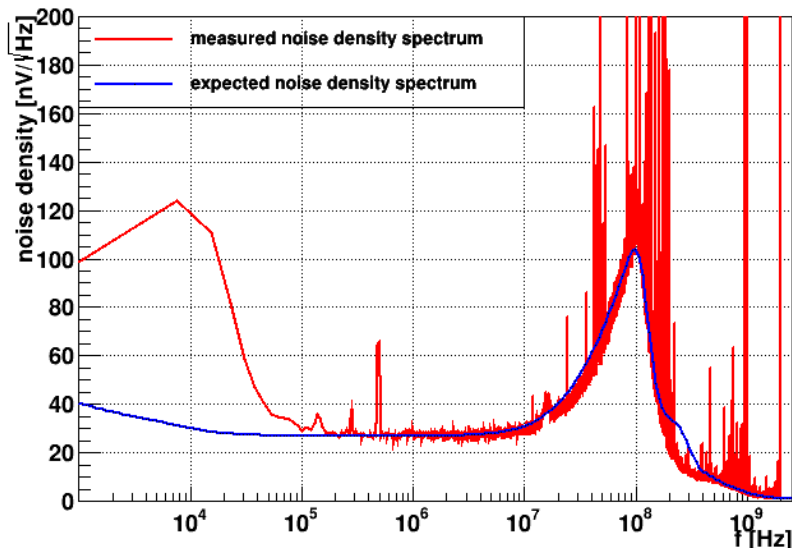


G10 output spectrum (1.6nH/cm, 2.4pF/cm)

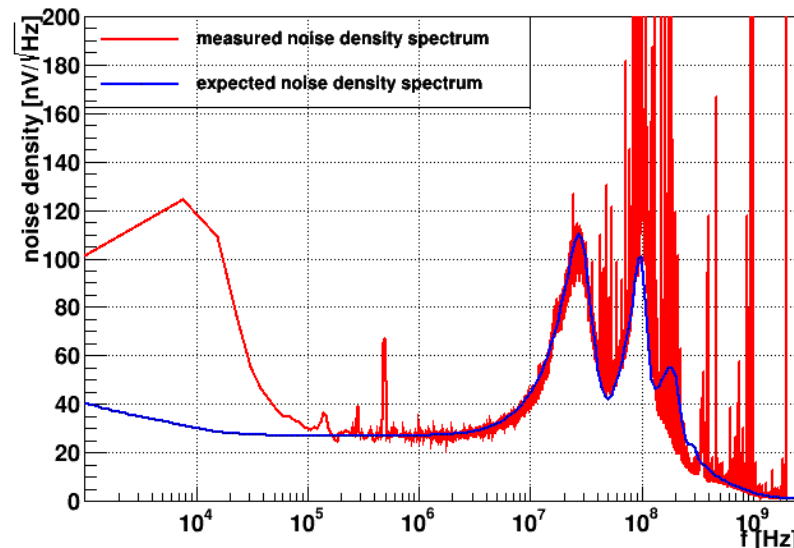


● Noise density spectra: Spice vs Measurements

F2fft-g10_noise-0pF_dB **No APD connected**

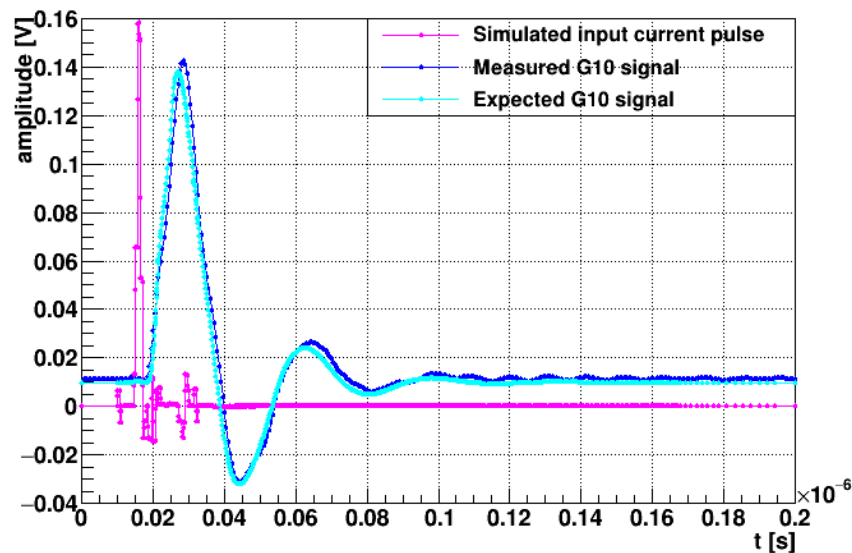


F2fft-g10_noise-164pF_dB **Fake APD connected**

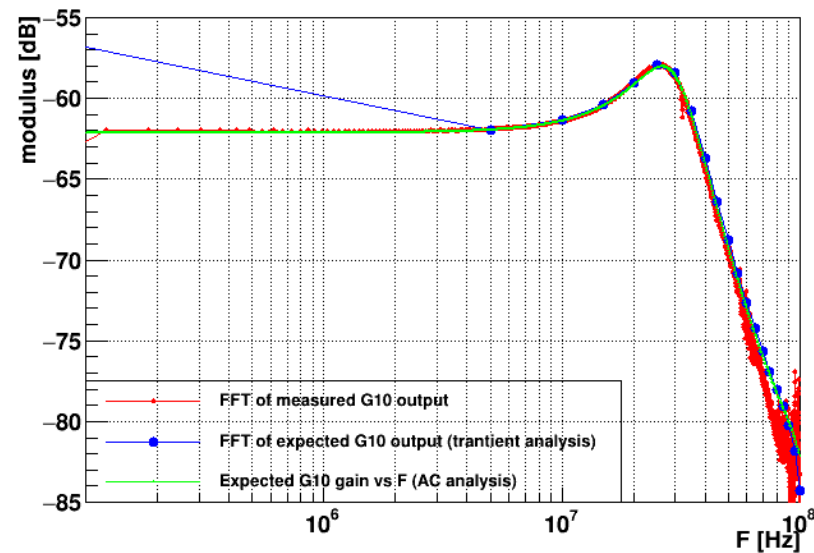


● Signal and spectrum: Spice vs Measurements

Simulation with 3.75nH and 2.5pF/cm

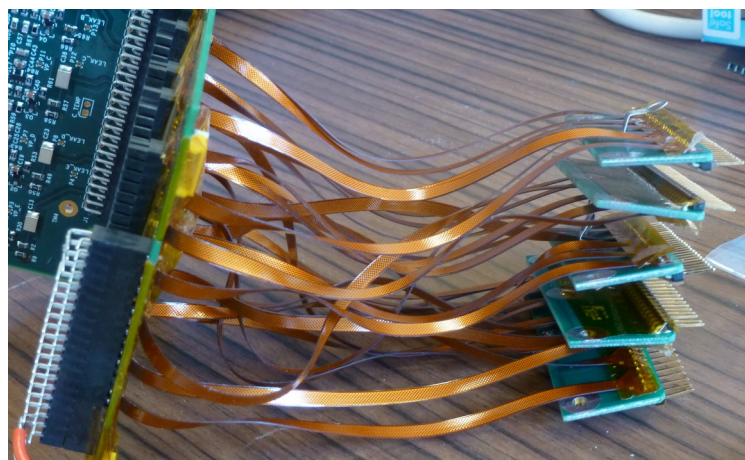
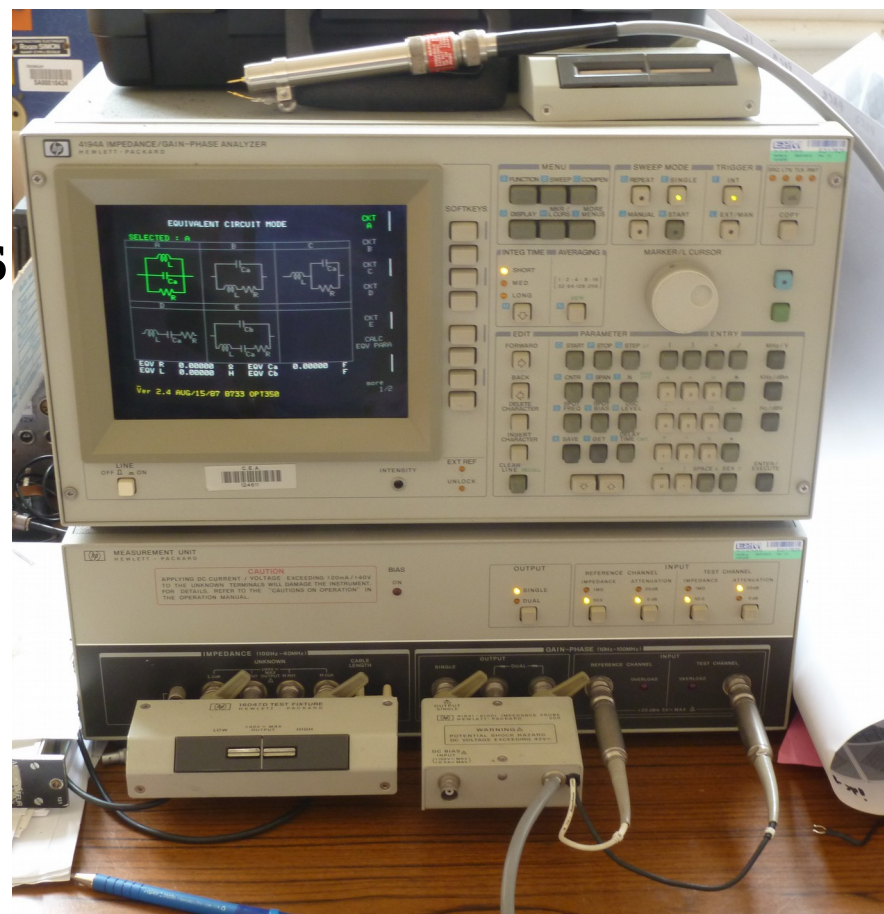


G10 output spectrum (3.75nH/cm, 2.5pF/cm)

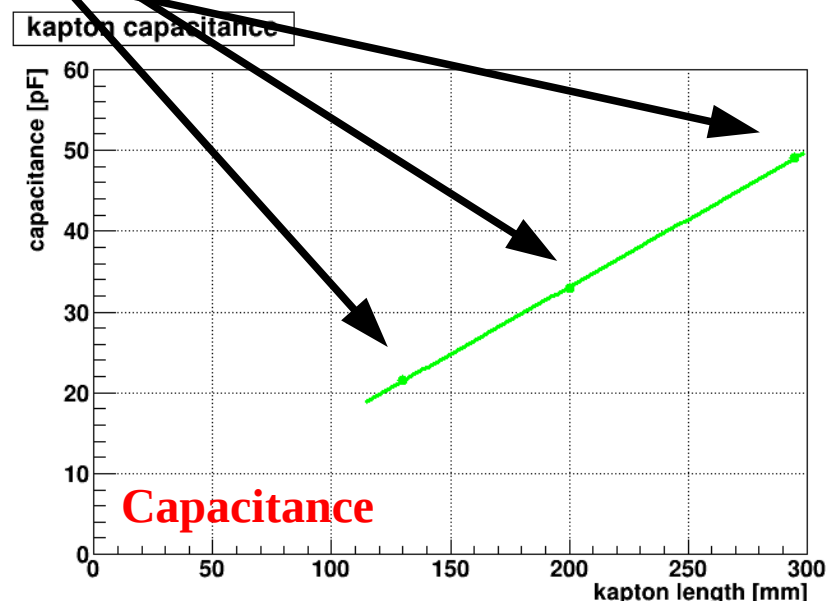
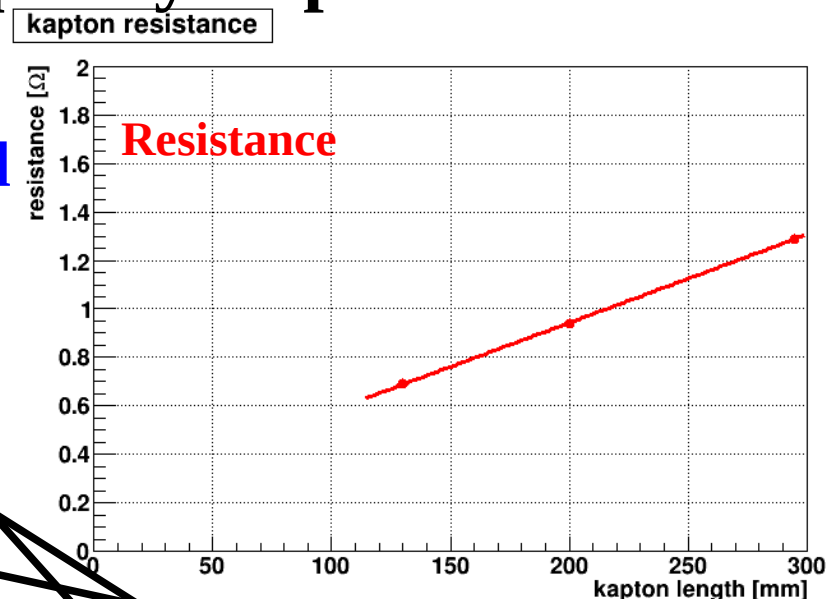
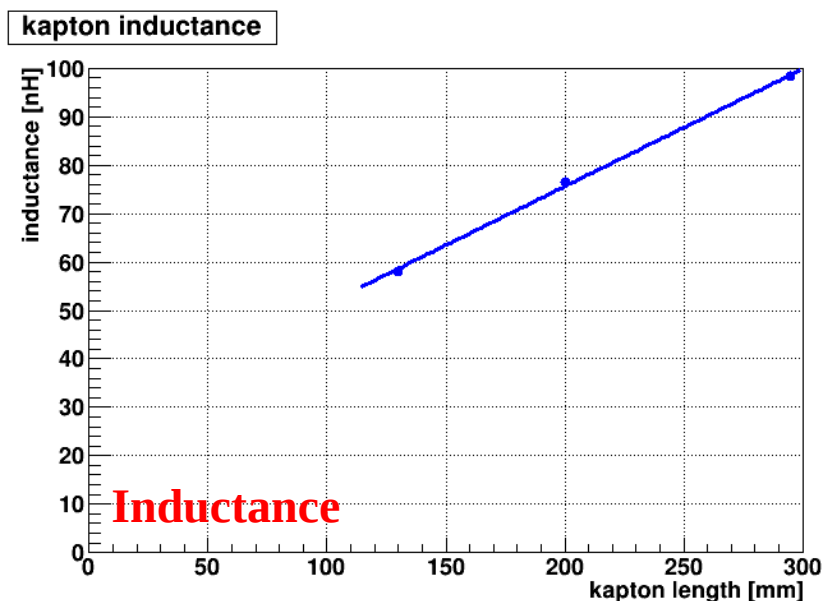


Kapton parameters

- Good spice-measurement agreement with
 - 3.75 nH/cm instead of 1.6nH/cm
 - 2.5 pF/cm instead 2.4pF/cm
- Make measurements on kaptons
 - Back to lab
 - ▶ Use HP4194 from past century
 - ▶ I/O is only screen or printer

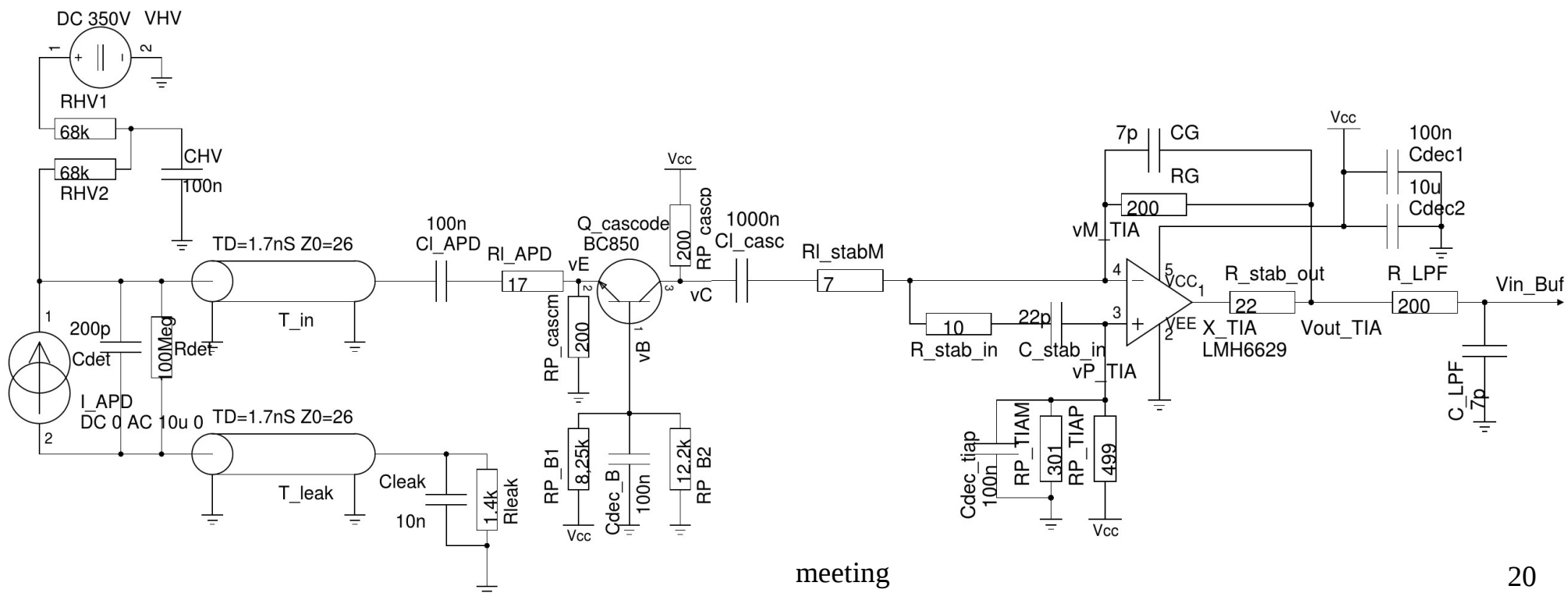


- Automatic measurement of frequency response
 - From 10 kHz to 100 MHz
 - Compute equivalent R-L-C model
- Measurements
 - Mother-board alone : 13cm
 - + Module 1 kapton : 70 mm
 - + Module 4 kapton : 165 mm



- Curves “R-L-C vs d” don't go through 0
 - Mother boards and capsules kaptons are different
- Mother board kaptons (d = 130 mm)
 - $R_{MB} = 53 \text{ m}\Omega/\text{cm}$
 - $L_{MB} = 4.5 \text{ nH/cm}$
 - $C_{MB} = 2.4 \text{ pF/cm}$
- APD capsule kaptons (d from 70 to 165 mm)
 - $R_{APD} = 35 \text{ m}\Omega/\text{cm}$
 - $L_{APD} = 2.4 \text{ nH/cm}$
 - $C_{APD} = 1.7 \text{ pF/cm}$
- Possible impedance mismatch at capsule connection
- Dramatic consequence:
 - Shift resonance frequency below 40 MHz
 - ▶ Inside signal frequency domain !

- New PCB with reduced parasitics
 - Optimized for low kapton parameters (not measured ones)
- Modified input stage
 - Possibility to insert a current buffer between APD and TIA
- Modified TIA stage
 - Implement compensation for phase margin recovery





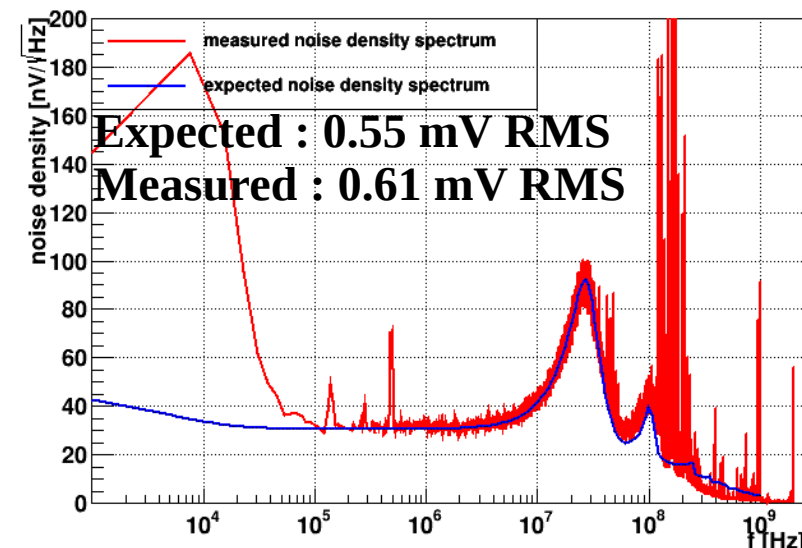
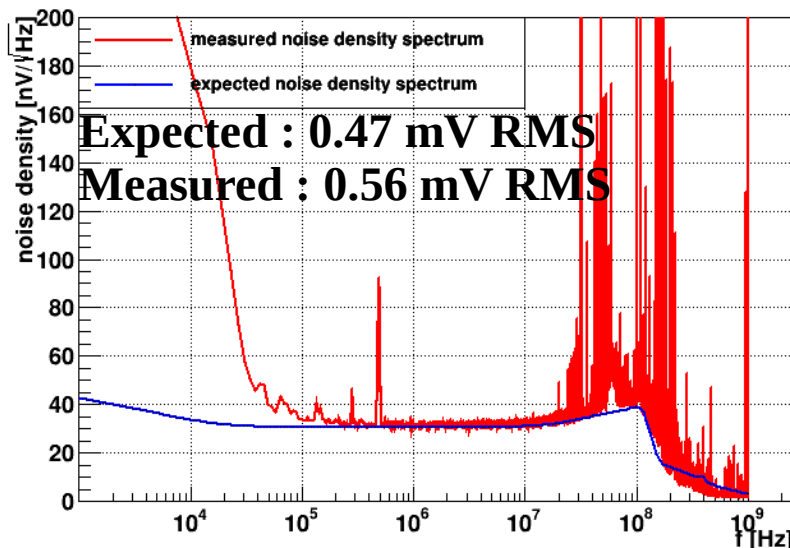
G1

TIA

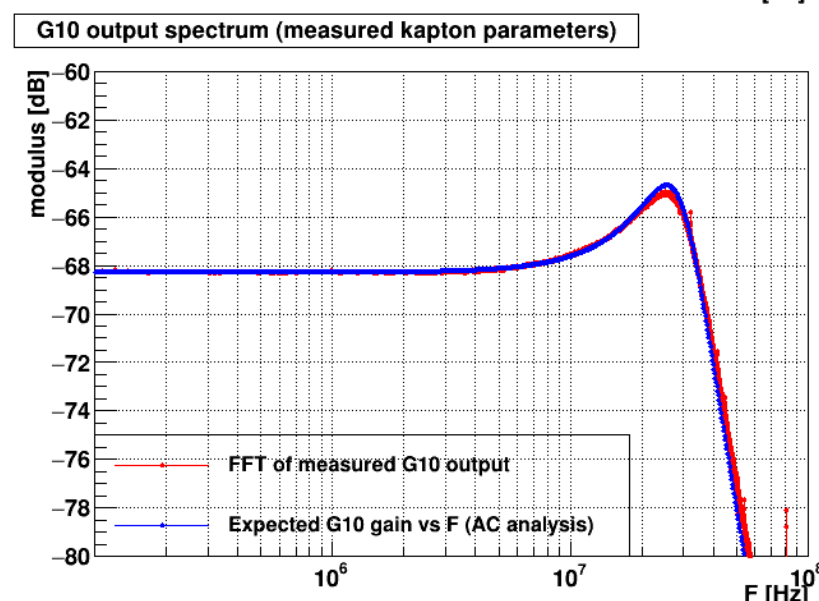
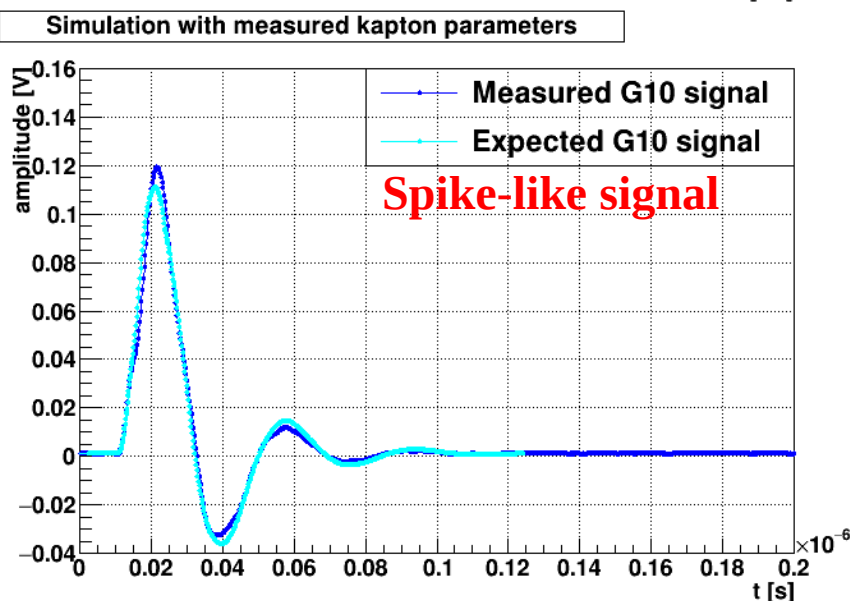
Current buffer

- Use measured kapton parameters

• Noise



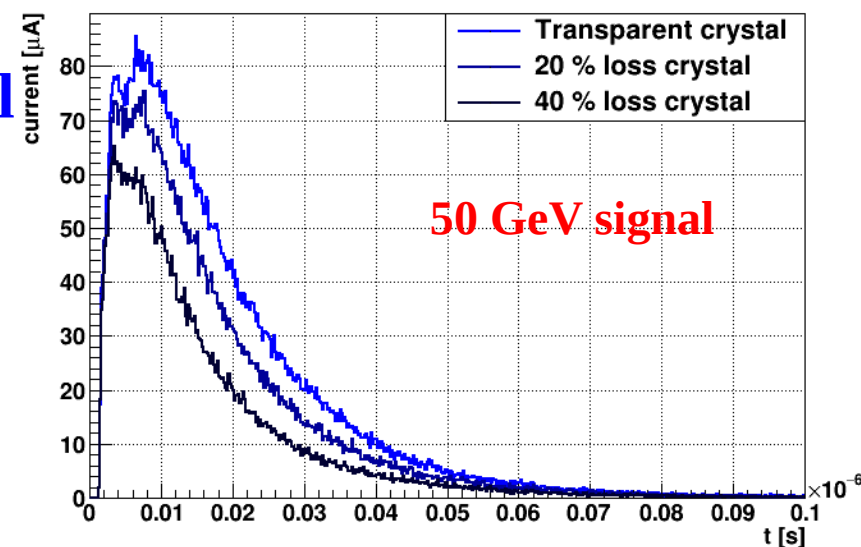
• Signal



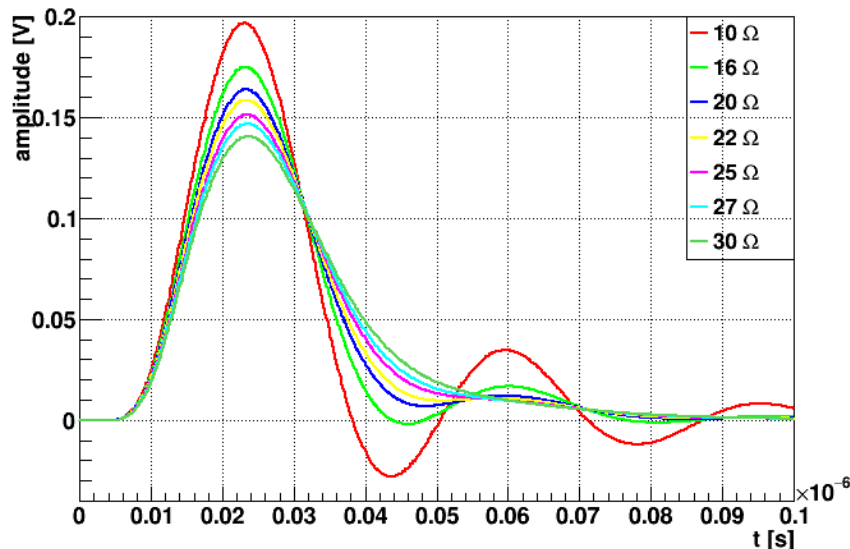
- **Goal**
 - Isolate TIA from APD connection
 - ▶ Gain stability
 - ▶ Less noise (hopefully)
- **Problems**
 - Design optimization with spice but:
 - ▶ Transistor spice models not reliable
 - Non predictive study
- **Work in progress**
 - Stay tuned

- Tune APD damping resistor
 - Look at expected scintillation signal
 - ▶ Home made photon tracking program
 - ▶ Generate spice input files for 50 GeV photon
 - Simulate TIA response

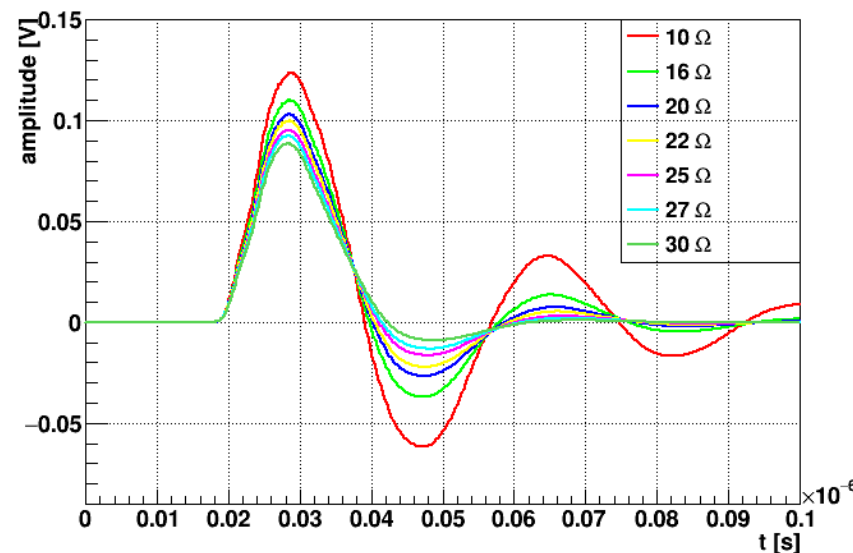
Photo current on APD, 50GeV e.m. deposition



TIA output for 50 GeV e.m. deposition

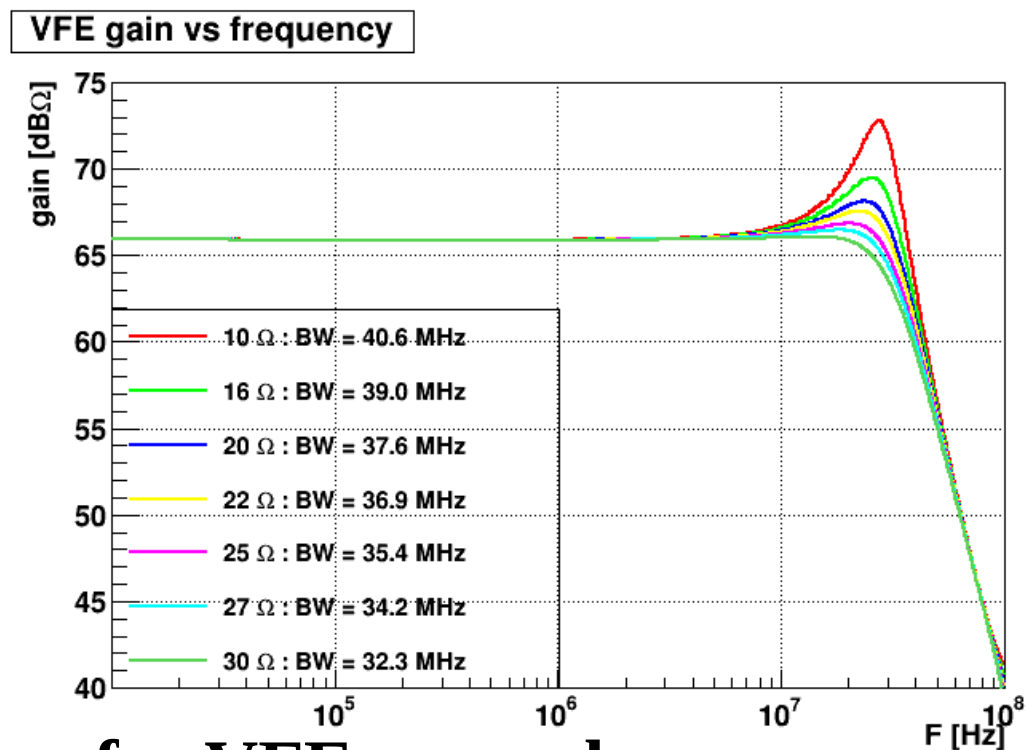


TIA output for spike signals



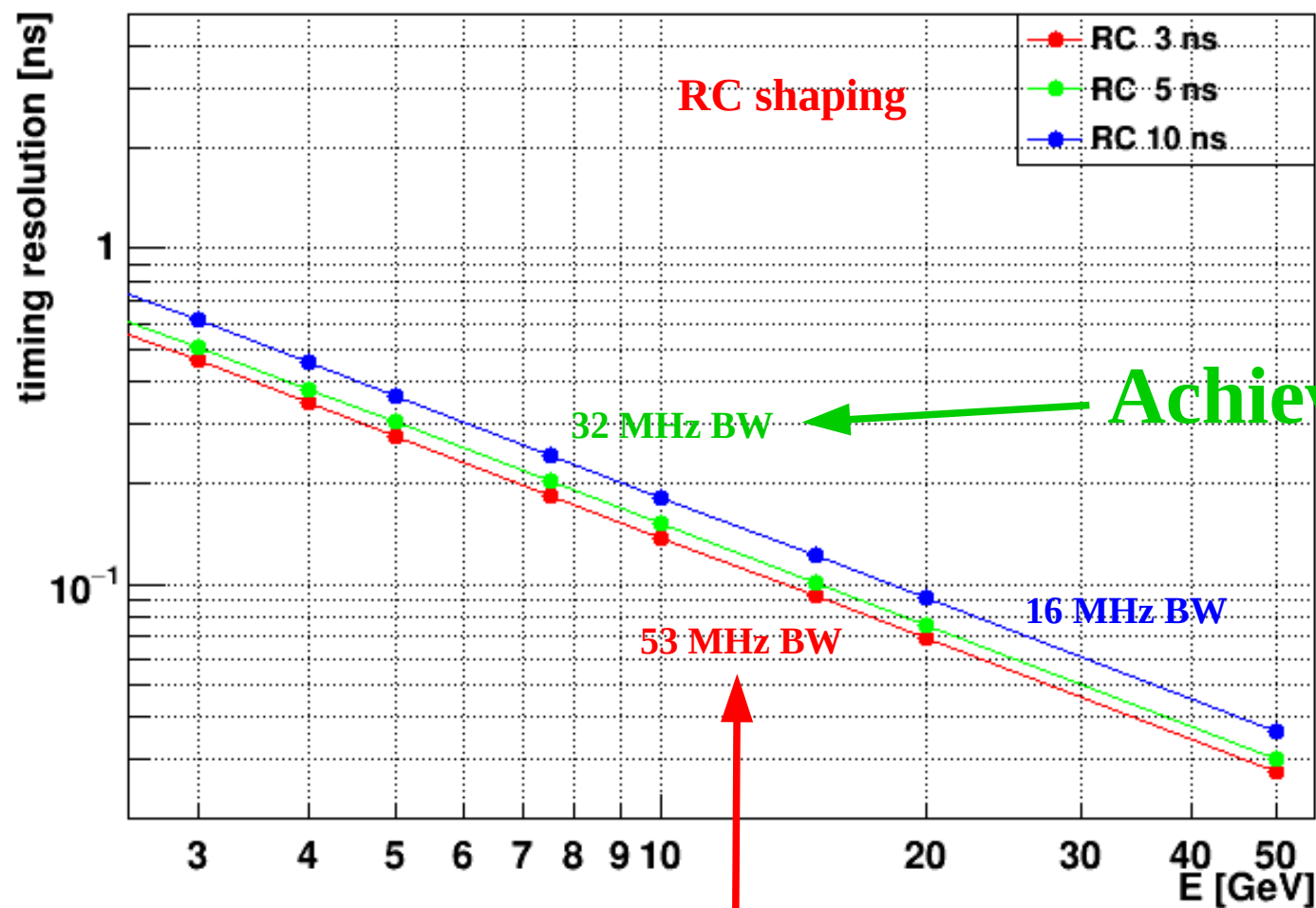
TIA bandwidth vs mitigation

- Adding serial resistor for kapton mitigation
 - Reduces TIA bandwidth



- Consequences for VFE upgrades :
 - 50 MHz bandwidth not achievable !
 - Upper most achievable electronics bandwidth : 40 MHz
 - Most probable electronics bandwidth 35 MHz

$I_{\text{dark}} = 100 \mu\text{A}$



Our dream

- Check “current buffer” architecture performances
- Connect APD and send light
 - 500 ps laser to simulate spike signal
- Equip 5 VFE boards
 - PCB in hands
 - 2/3 weeks work
- Put in TB
 - Measure scintillation/spike shapes
 - ▶ Check timing performances
 - Measure noise structure
 - ▶ Different APD leakage current
- Implement models/shapes in simulation program
- Check performances with Physics (CMSSW)

- **VFE upgrade performances limited by existing connections to crystals**
 - **Have to deal with 75-100 nH inductances**
 - ▶ **System bandwidth limited to ~35 MHz**

- **Preliminary step for:**
 - **Feasibility study of a TIA-asic with TSMC 130nm technology**
 - ▶ **Study well advanced in Saclay**
 - ▶ **All simulations OK so far**
 - ▶ **Signature of CERN-TSMC NDA to go further**
 - **More details at ACES-2016**

- Rock solid inputs mandatory for TDR redaction.
 - APD+kaptons+motherboard characterization
 - Shape measurement for scintillation and spikes
 - Noise models validation
- Test-beam measurements with TIA can allow to do this
 - 50 35 MHz BW, reasonable noise level (200 MeV)
 - Multi-Gs/sec acquisition to simulate all scenarios
 - Fast timing setup to get the timing performances
- TIA with Op-Amps designed
 - Ready to go to TB with 3 weeks notice
 - ▶ Fine tuning in progress